



**SOT-23-3L Plastic-Encapsulate MOSFETS**

**MK3407A**

**P-Channel 30-V(D-S) MOSFET**

V(BR)DSS	RDS(on)MAX	ID
-30 V	60mΩ@-10V	-4.1A
	80mΩ@-4.5V	

**FEATURE**

※ TrenchFET Power MOSFET

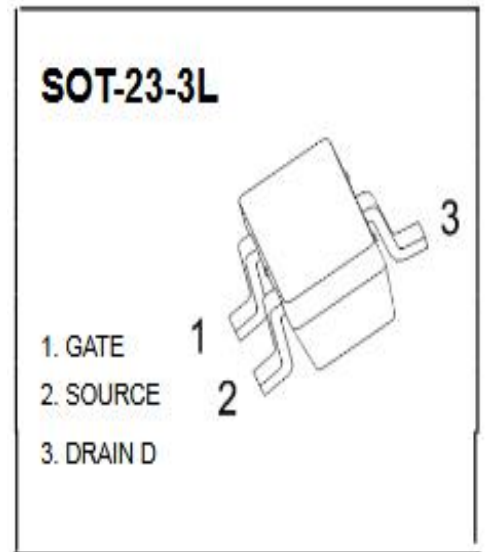
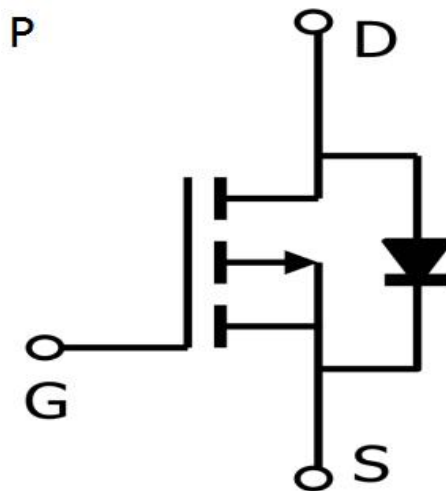
**APPLICATION**

- ※ Load Switch for Portable Devices
- ※ DC/DC Converter

**MARKING**



**Equivalent Circuit**



**Maximum ratings ( Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	-30	V
Gate-Source Voltage	VGS	±20	
Continuous Drain Current	ID	-4.1	A
Pulsed Diode Current	IDM	-15	
Continuous Source-Drain Current(Diode Conduction)	IS	-0.8	
Power Dissipation	PD	1.4	W
Thermal Resistance from Junction to Ambient (t≤5s)	RθJA	125	°C/W
Operating Junction	TJ	150	°C
Storage Temperature	TSTG	-55~+150	°C



MOSFET ELECTRICAL CHARACTERISTICS

Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)

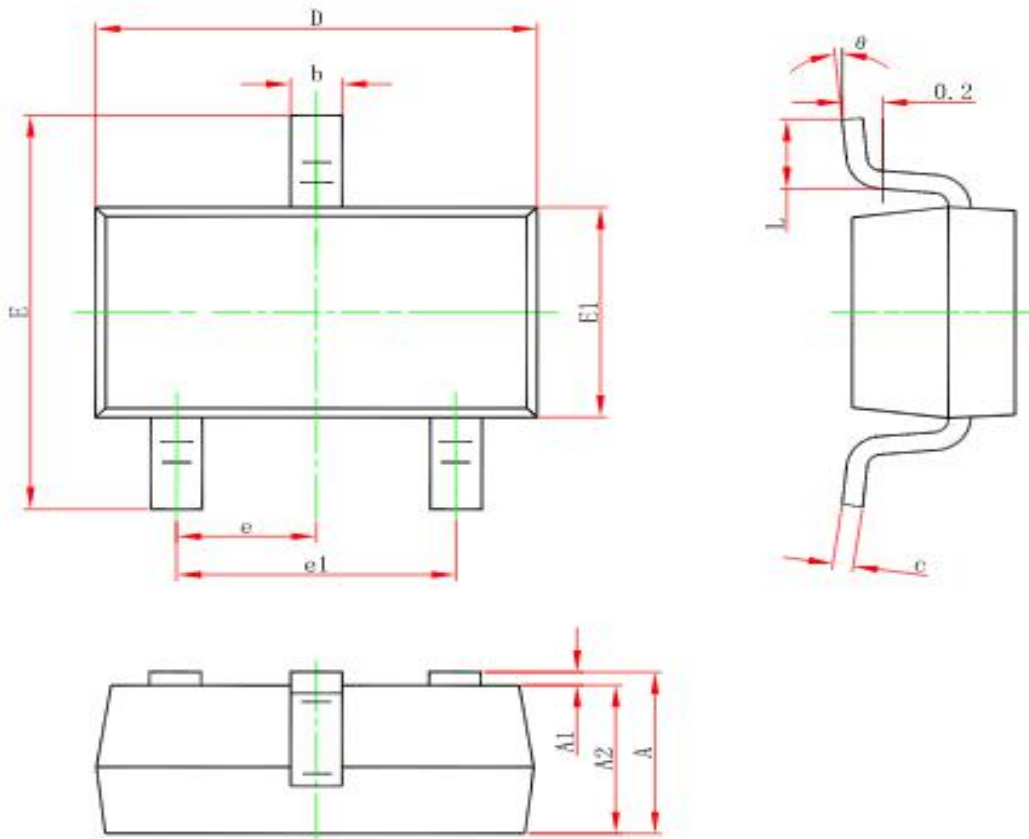
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	<b>V(BR)DSS</b>	VGS = 0V, ID = -250μA	-30			V
Gate-source threshold voltage	<b>VGS(th)</b>	VDS =VGS, ID = -250μA	-1		-2	V
Gate-source leakage	<b>IGSS</b>	VDS =0V, VGS = ±20V			±100	nA
Zero gate voltage drain current	<b>IDSS</b>	VDS = -24V, VGS =0V			-1	μA
Drain-source on-state resistancea	<b>RDS(on)</b>	VGS = -10V, ID = -4.1A		53	60	mΩ
		VGS = -4.5V, ID = -3A		63	80	mΩ
Forward transconductancea	<b>gfs</b>	VDS = -4.5V, ID = -4.1A		10		S
Diode forward voltage	<b>VSD</b>	IS=-1A,VGS=0V	-0.5	-0.8	-1.1	V
<b>Dynamic</b>						
Input capacitance	<b>Ciss</b>	VDS = -15V,VGS =0V, f=1MHz		520		pF
Output capacitance	<b>Coss</b>			100		pF
Reverse transfer capacitanceb	<b>Crss</b>			65		pF
Total gate charge	<b>Qg</b>	VDS = -15V,VGS = - 4.5V, ID = - 4.1A		9.4		nC
Gate-source charge	<b>Qgs</b>			2		nC
Gate-drain charge	<b>Qgd</b>			3		nC
Gate resistance	<b>Rg</b>	f=1MHz		7.5		Ω
<b>Switchingb</b>						
Turn-on delay time	<b>td(on)</b>	VDS= -15V RL=3Ω, ID ≈ 1-A, VGEN= -4.2V,Rg=3Ω		705		ns
Rise time	<b>tr</b>			5		ns
Turn-off delay time	<b>td(off)</b>			19		ns
Fall time	<b>tf</b>			7		ns
<b>Drain-source body diode characteristics</b>						
Continuous Source-Drain Diode Current	<b>IS</b>	Tc=25°C			-1.1	A
Pulsed Diode forward Curren	<b>ISM</b>				-20	A

**Note :**

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 5 sec.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.



SOT-23-3L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
theta	0°	8°	0°	8°



Typical Characteristics:

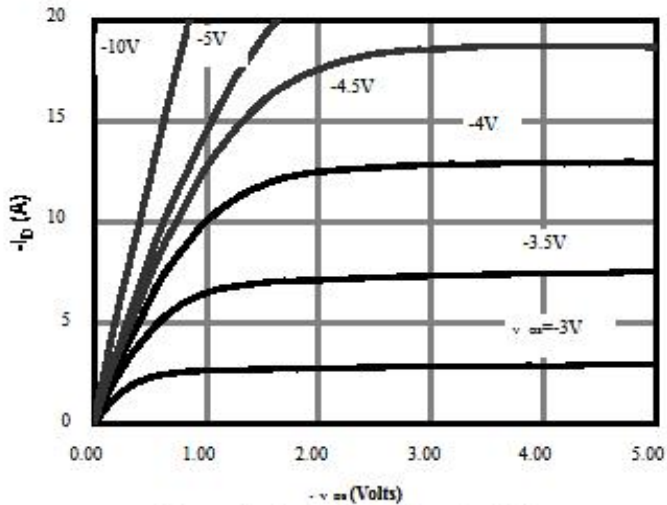


Figure 1: On-Region Characteristics

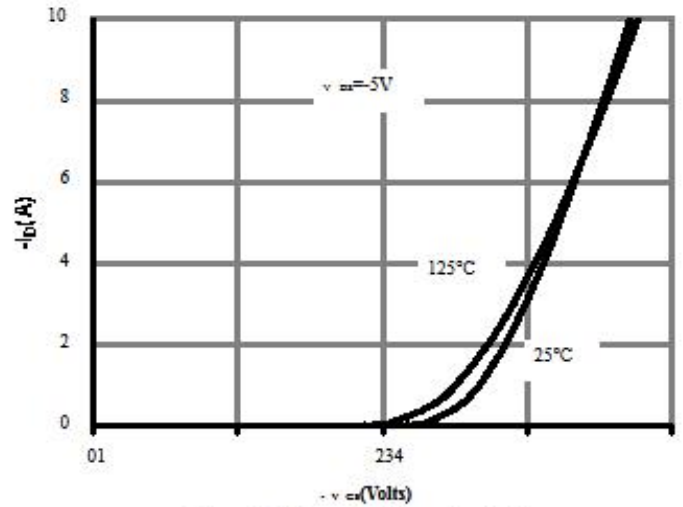


Figure 2: Transfer Characteristics

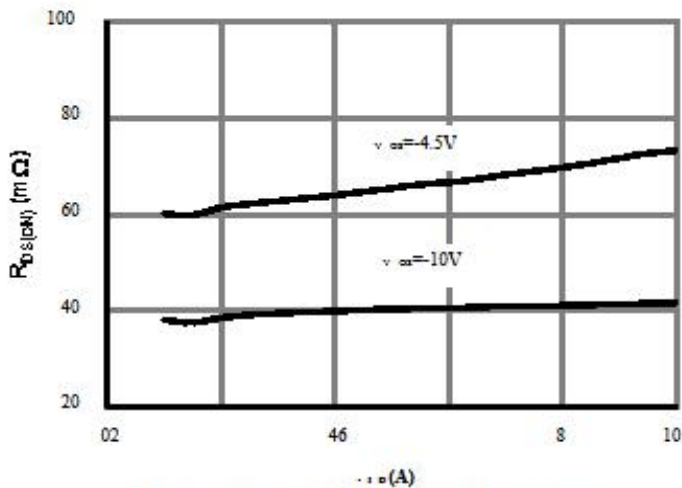


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

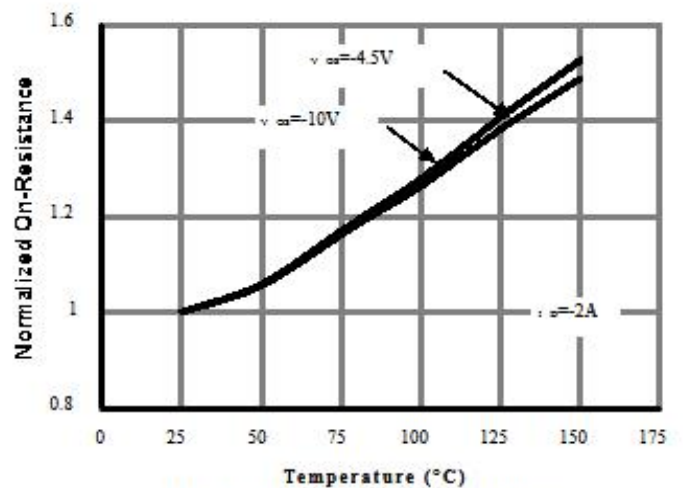


Figure 4: On-Resistance vs. Junction Temperature

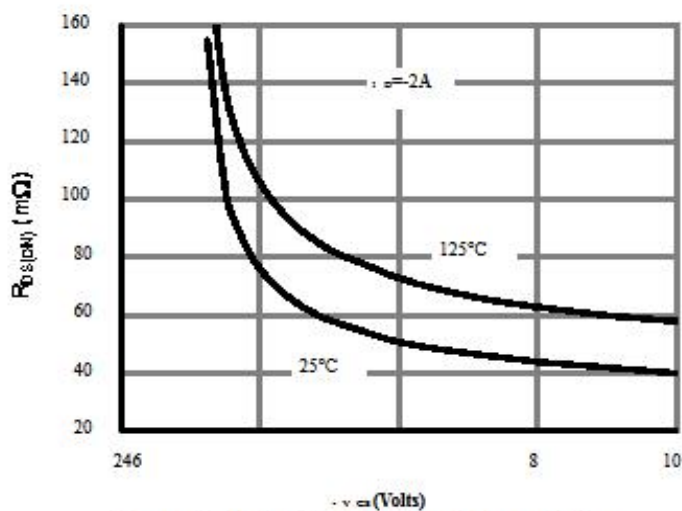


Figure 5: On-Resistance vs. Gate-Source Voltage

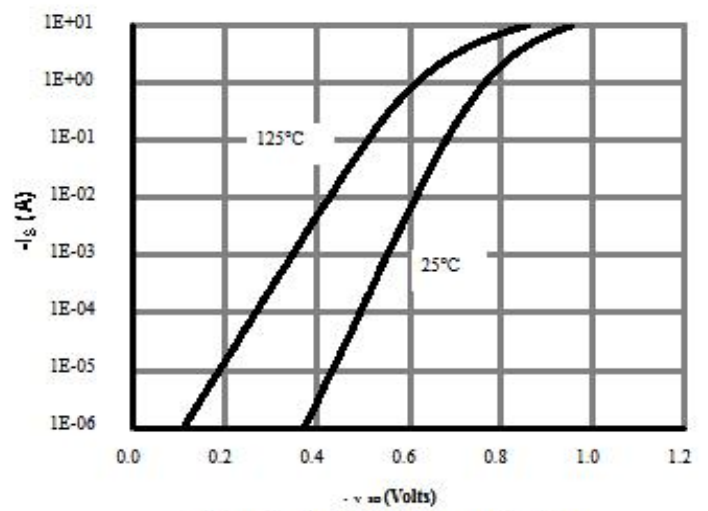


Figure 6: Body-Diode Characteristics



Typical Characteristics :

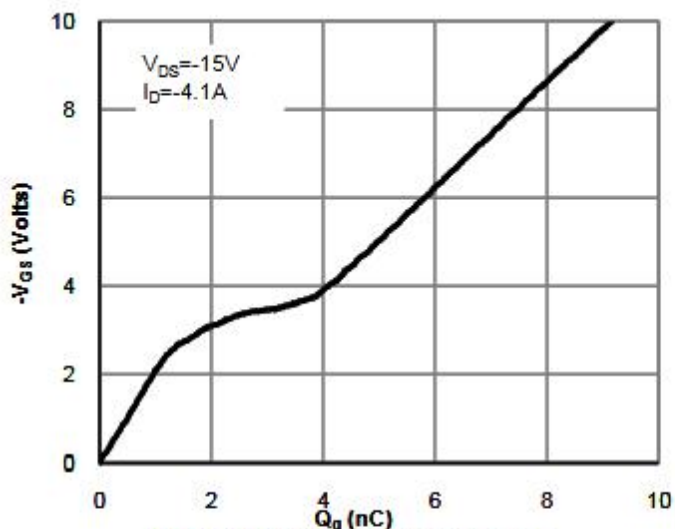


Figure 7: Gate-Charge Characteristics

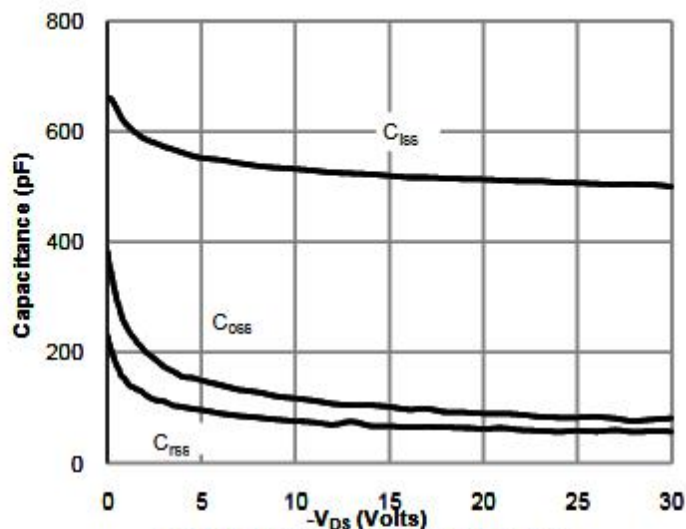


Figure 8: Capacitance Characteristics

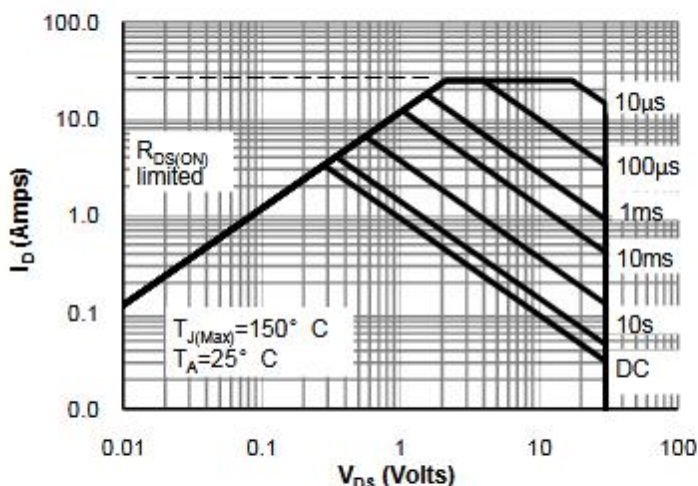


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

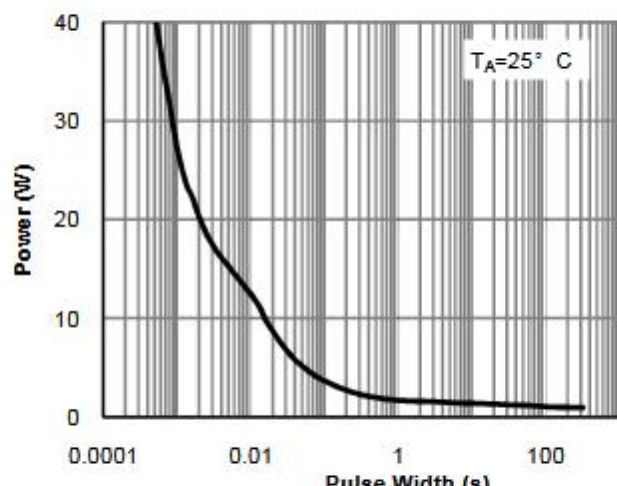


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

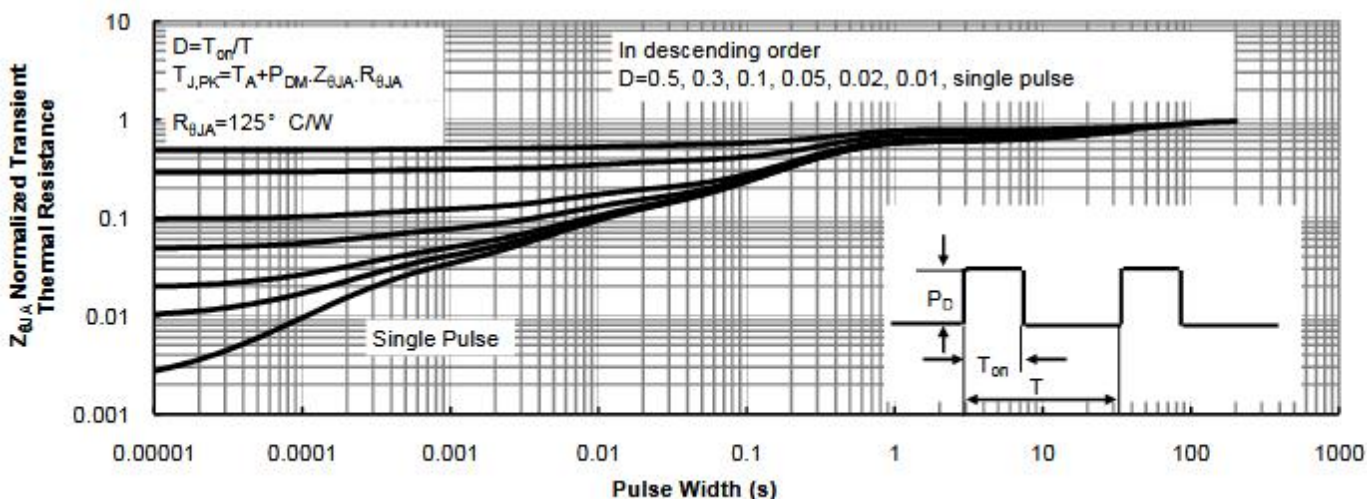


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)